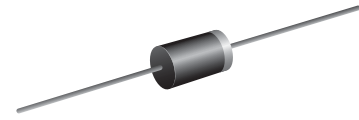


VOLTAGE RANGE: 100V
CURRENT: 5.0 A

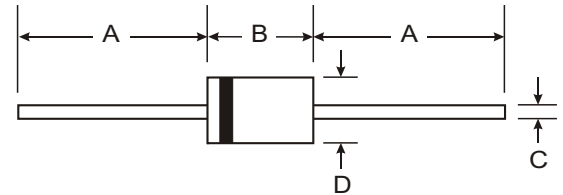


Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-201AD		
Dim	Min	Max
A	25.40	—
B	8.50	9.53
C	0.96	1.06
D	4.80	5.21
All Dimensions in mm		



Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

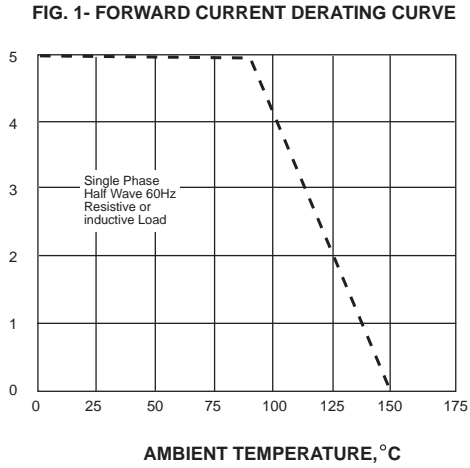
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SB5A0	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	100	Volts
Maximum RMS voltage	V _{RMS}	70	Volts
Maximum DC blocking voltage	V _{DC}	100	Volts
Maximum average forward rectified current 0.375" (9.5mm) lead length(see fig.1)	I _(AV)	5.0	Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	150.0	Amps
Maximum instantaneous forward voltage at 5.0A	V _F	0.85	Volts
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	10.0	mA
Typical junction capacitance (NOTE 1)	C _J	400	pF
Typical thermal resistance (NOTE 2)	R _{θJA}	25.0	°C/W
Operating junction temperature range	T _J	-65 to +150	°C
Storage temperature range	T _{STG}	-65 to +150	°C

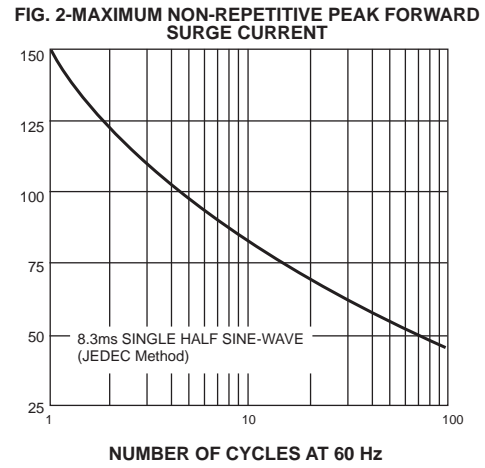
Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

RATINGS AND CHARACTERISTIC CURVES SB5A0

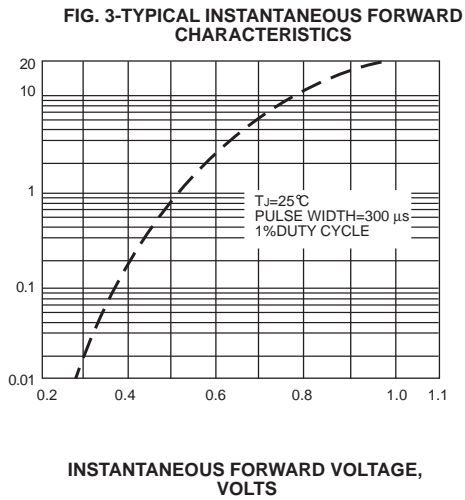
AVERAGE FORWARD RECTIFIED CURRENT, AMPERES



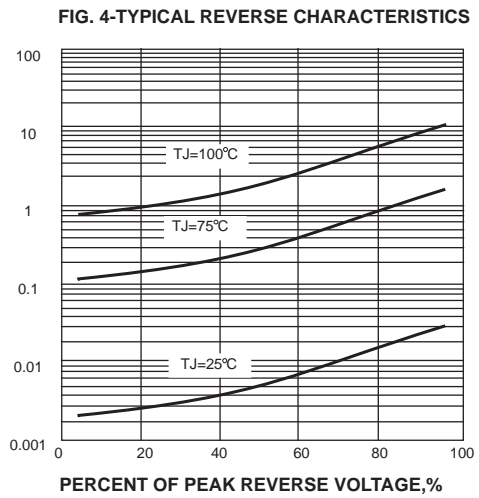
PEAK FORWARD SURGE CURRENT, AMPERES



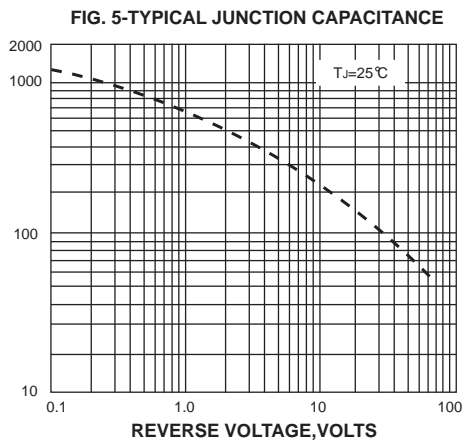
INSTANTANEOUS FORWARD CURRENT, AMPERES



INSTANTANEOUS REVERSE CURRENT, MILLIAMPERES



JUNCTION CAPACITANCE, pF



TRANSIENT THERMAL IMPEDANCE, °C/W

